

**UTC** UNISONIC TECHNOLOGIES CO., LTD

2SC4467

NPN EPITAXIAL SILICON TRANSISTOR

# SILICON NPN TRIPLE DIFFUSED PLANAR TRANSISTOR

#### DESCRIPTION

The UTC 2SC4467 is a silicon NPN triple diffused planar transistor, it uses UTC's advanced technology to provide the customers with high DC current gain and high collector-base breakdown voltage, etc.

The UTC 2SC4467 is suitable for audio and general purpose, etc.

#### **FEATURES**

\* High DC current gain

\* High collector-base breakdown voltage

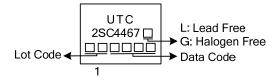
#### **ORDERING INFORMATION**

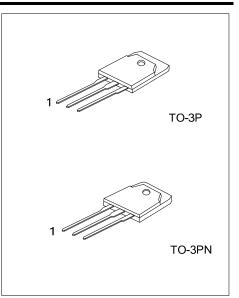
Ordering Number		Dookago	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2SC4467L-x-T3P-T	2SC4467G-x-T3P-T	TO-3P	В	С	Е	Tube	
2SC4467L-x-T3N-T	2SC4467G-x-T3N-T	TO-3PN	В	С	Е	Tube	
Note: Din Assignment: B: Base C: Collector E: Emitter							

Note: Pin Assignment: B: Base C: Collector E: Emitter

2SC4467L-x-T3P-T (1)Packing Type (2)Package Type (3)Rank (4)Green Package	<ul> <li>(1) T: Tube</li> <li>(2) T3P: TO-3P, T3N: TO-3PN</li> <li>(3) x: reference to Classification of h<sub>FE</sub></li> <li>(4) L: Lead Free, G: Halogen Free and Lead Free</li> </ul>
(4)Green Package	(4) L: Lead Free, G: Halogen Free and Lead Free

#### MARKING





### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	120	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current	Ι <sub>C</sub>	8	А
Base Current	Ι <sub>Β</sub>	3	А
Collector Power Dissipation (T <sub>C</sub> =25°C)	Pc	80	W
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)

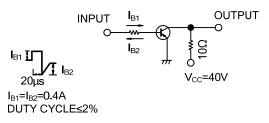
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current		I <sub>CBO</sub>	V <sub>CB</sub> =160V			10	μA
Emitter Cut-Off Current		I <sub>EBO</sub>	V <sub>EB</sub> =6V			10	μA
Collector-Emitter Breakdown Voltage		BV <sub>CEO</sub>	I <sub>C</sub> =50mA	120			V
DC Current Gain		h <sub>FE</sub>	V <sub>CE</sub> =4V, I <sub>C</sub> =3A	50			
Collector-Emitter Saturation Voltage		V <sub>CE(sat)</sub>	I <sub>C</sub> =3A, I <sub>B</sub> =0.3A			1.5	V
Current Gain Bandwidth Product		f⊤	V <sub>CE</sub> =12V, I <sub>E</sub> =-0.5A		20		MHz
Output Capacitance		Cob	V <sub>CB</sub> =10V, f=1MHz		200		pF
Switching time	Turn-on time	t <sub>on</sub>	V <sub>CC</sub> =40V, R∟=10Ω, I <sub>C</sub> =4A, I <sub>B1</sub> =0.4A I <sub>B2</sub> =0.4A		0.13		μS
	Storage time	ts			3.50		μS
	Fall time	t⊢			0.32		μS

### CLASSIFICATION OF h<sub>FE</sub>

I	RANK	0	Р	Y	
	RANGE	50~100	70~140	90~180	



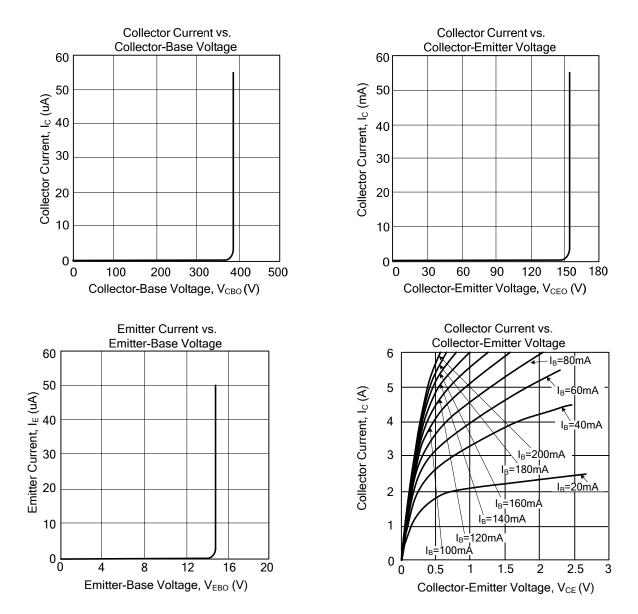
## TEST CIRCUIT





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### TYPICAL CHARACTERISTICS



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